



# HBAS16

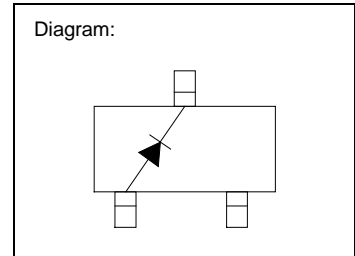
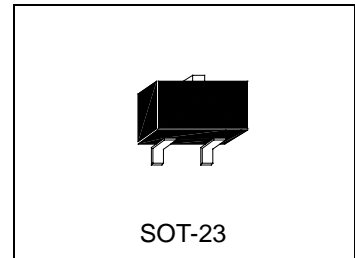
HIGH-SPEED SWITCHING DIODE

## Description

- The HBAS16 is designed for high-speed switching application in hybrid thick and thin-film circuits.
- The devices is manufactured by the silicon epitaxial planar process and packed in a plastic surface mount package.

## Features

- Small SMD Package (SOT-23)
- Low Forward Voltage
- Fast Reverse Recovery Time
- Small Total Capacitance



## Absolute Maximum Ratings

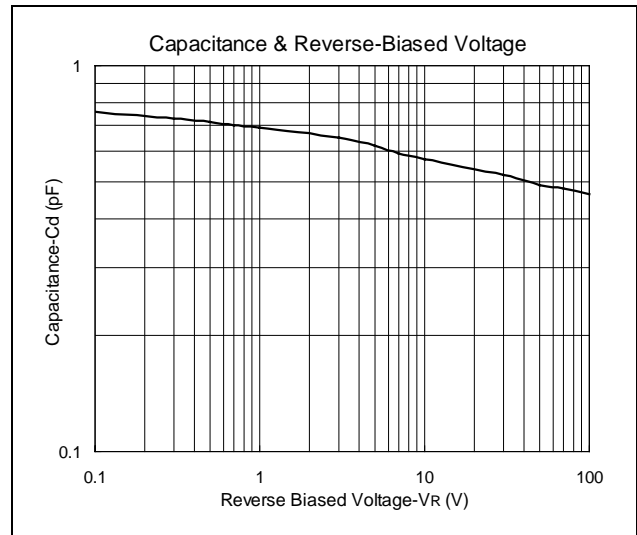
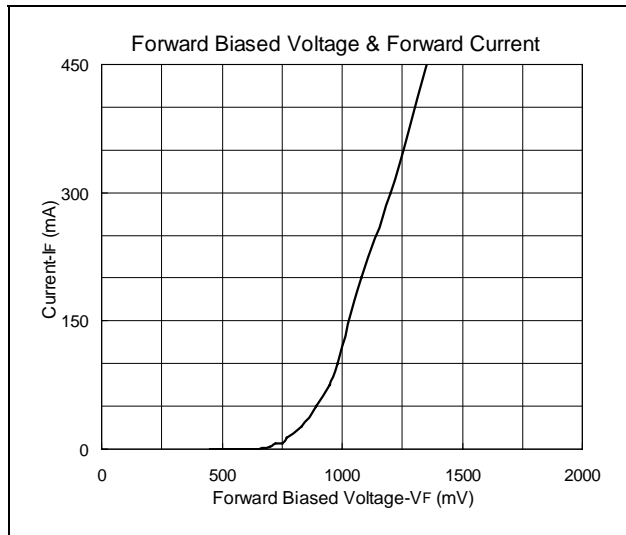
- Maximum Temperatures
  - Storage Temperature ..... -65~+150 °C
  - Junction Temperature ..... +150 °C
- Maximum Power Dissipation
  - Total Power Dissipation (T<sub>A</sub>=25°C) ..... 200 mW
- Maximum Voltages and Currents (T<sub>A</sub>=25°C)
  - Reverse Voltage..... 75 V
  - Repetitive Reverse Voltage ..... 85 V
  - Forward Current..... 250 mA
  - Repetitive Forward Current ..... 500 mA
  - Forward Surge Current (1ms)..... 1 A

## Electrical Characteristics (T<sub>A</sub>=25°C)

Characteristic	Symbol	Condition	Min.	Max.	Unit
Reverse Breakdown Voltage	V <sub>(BR)</sub>	I <sub>R</sub> =100uA	75	-	V
Forward Voltage	V <sub>F(1)</sub>	I <sub>F</sub> =1mA	-	715	mV
	V <sub>F(2)</sub>	I <sub>F</sub> =10mA	-	855	mV
	V <sub>F(3)</sub>	I <sub>F</sub> =50mA	-	1000	mV
	V <sub>F(4)</sub>	I <sub>F</sub> =150mA	-	1250	mV
Reverse Current	I <sub>R</sub>	V <sub>R</sub> =75V	-	1	uA
Total Capacitance	C <sub>T</sub>	V <sub>R</sub> =0, f=1MHZ	-	2	pF
Reverse Recovery Time	T <sub>rr</sub>	I <sub>F</sub> =I <sub>R</sub> =10mA, R <sub>L</sub> =100Ω, measured at I <sub>R</sub> =1mA	-	6	nS



## Characteristics Curve





### SOT-23 Dimension

3-Lead SOT-23 Plastic  
Surface Mounted Package  
HSMC Package Code: N

**Marking:**

Pb Free Mark  
 Pb-Free: "•" (Note)  
 Normal: None

Note: Pb-free product can distinguish by the green label or the extra description on the right side of the label.

Pin Style: 1.Anode 2.NC 3.Cathode

Material:

- Lead solder plating: Sn60/Pb40 (Normal), Sn/3.0Ag/0.5Cu or Pure-Tin (Pb-free)
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

DIM	Min.	Max.
A	2.80	3.04
B	1.20	1.60
C	0.89	1.30
D	0.30	0.50
G	1.70	2.30
H	0.013	0.10
J	0.085	0.177
K	0.32	0.67
L	0.85	1.15
S	2.10	2.75
V	0.25	0.65

\*: Typical, Unit: mm

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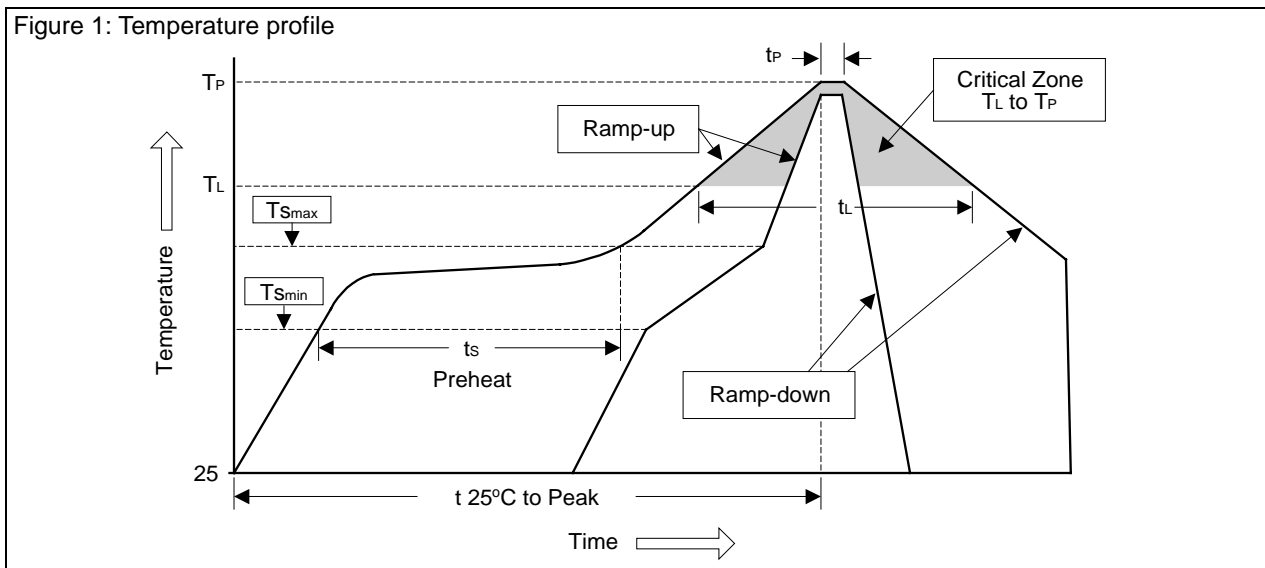
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## Soldering Methods for HSMC's Products

1. Storage environment: Temperature=10°C~35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate ( $T_L$ to $T_p$ )	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min ( $T_{smin}$ )	100°C	150°C
- Temperature Max ( $T_{smax}$ )	150°C	200°C
- Time (min to max) ( $t_s$ )	60~120 sec	60~180 sec
$T_{smax}$ to $T_L$		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature ( $T_L$ )	183°C	217°C
- Time ( $t_L$ )	60~150 sec	60~150 sec
Peak Temperature ( $T_p$ )	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature ( $t_p$ )	10~30 sec	20~40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

### 3. Flow (wave) soldering (solder dipping)

Products	Peak temperature	Dipping time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec